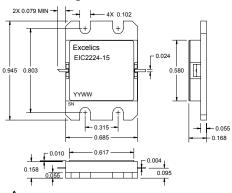


ISSUED 04/04/2006

2.20 – 2.40 GHz 15W Internally Matched Power FET

FEATURES

- 2.20- 2.40GHz Bandwidth •
- Input/Output Impedance Matched to 50 Ohms •
- +42.5 dBm Output Power at 1dB Compression •
- 13.0 dB Power Gain at 1dB Compression •
- 35% Power Added Efficiency •
- Hermetic Metal Flange Package •
- 100% Tested for DC, RF, and R_{TH} •



EIC2224-15

ELECTRICAL CHARACTERISTICS ($T_a = 25^{\circ}C$) Caution! ESD sensitive device.

SYMBOLS	PARAMETERS/TEST CONDITIONS ¹	MIN	ТҮР	MAX	UNIT
P _{1dB}	Output Power at 1dB Compressionf = 2.20-2.40GH V_{DS} = 10V, $I_{DSQ} \approx 4.6A$	^{lz} 41.5	42.5		dBm
G _{1dB}		lz 12.0	13.0		dB
∆G	Gain Flatnessf = 2.20-2.40GH V_{DS} = 10V, $I_{DSQ} \approx 4.6A$	lz		±0.6	dB
PAE	Power Added Efficiency at 1dB Compression V_{DS} = 10V, $I_{DSQ} \approx 4.6A$ f = 2.20-2.40GH	z	35		%
Id _{1dB}	Drain Current at 1dB Compression f = 2.20-2.40GHz	Z	4.8	5.4	А
I _{DSS}	Saturated Drain Current $V_{DS} = 3 V, V_{GS} = 0 V$		8.6	10.8	А
V _P	Pinch-off Voltage $V_{DS} = 3 V, I_{DS} = 86m/$	Ą	-2.5	-4.0	V
R _{TH}	Thermal Resistance ²		1.7	1.9	°C/W

Note: 1. Tested with 25 Ohm gate resistor. 2. Overall Rth depends on case mounting.

ABSOLUTE MAXIMUM RATING^{1,2}

SYMBOLS	PARAMETERS	ABSOLUTE ¹	CONTINUOUS ²
Vds	Drain-Source Voltage	15V	10V
Vgs	Gate-Source Voltage	-5V	-4V
lgsf	Forward Gate Current	192mA	64mA
lgsr	Reserve Gate Current	-33mA	-11mA
Pin	Input Power	42.0dBm	@ 3dB Compression
Tch	Channel Temperature	175 °C	175 °C
Tstg	Storage Temperature	-65 to +175 °C	-65 to +175 °C
Pt	Total Power Dissipation	79W	79W

Note: 1. Exceeding any of the above ratings may result in permanent damage.

2. Exceeding any of the above ratings may reduce MTTF below design goals.